

## Tutorial Class 6

Q1.

- (a) Using the characteristics of Fig. 3.8, determine the resulting collector current if  $I_E = 3 \text{ mA}$  and  $V_{CB} = 10 \text{ V}$ .
- (b) Using the characteristics of Fig. 3.8, determine the resulting collector current if  $I_E$  remains at  $3 \text{ mA}$  but  $V_{CB}$  is reduced to  $2 \text{ V}$ .

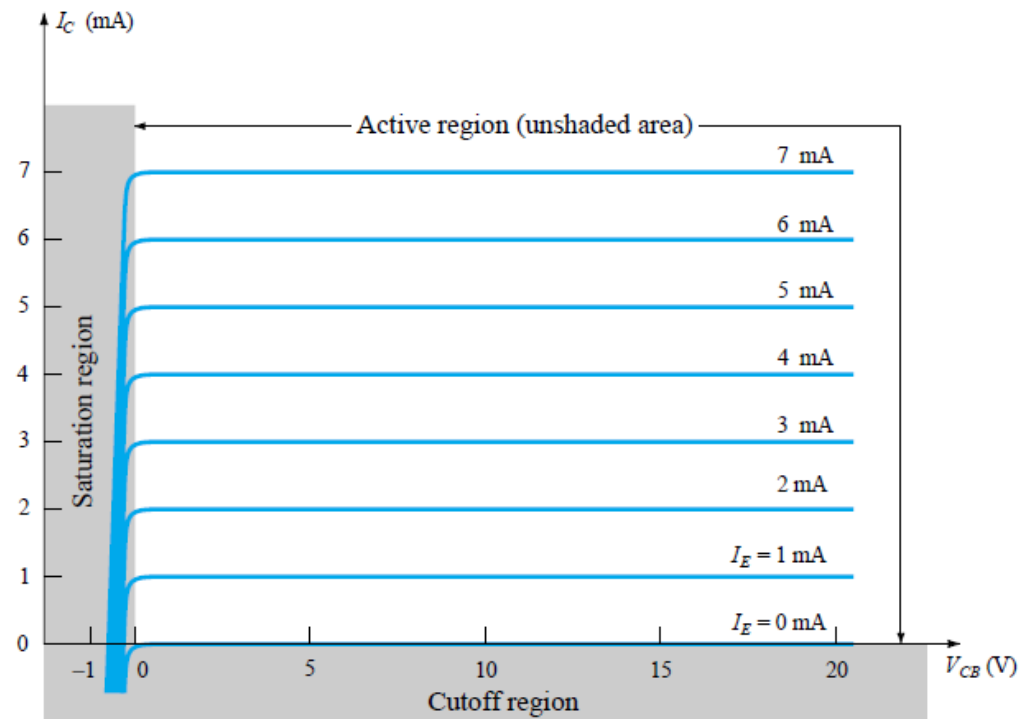
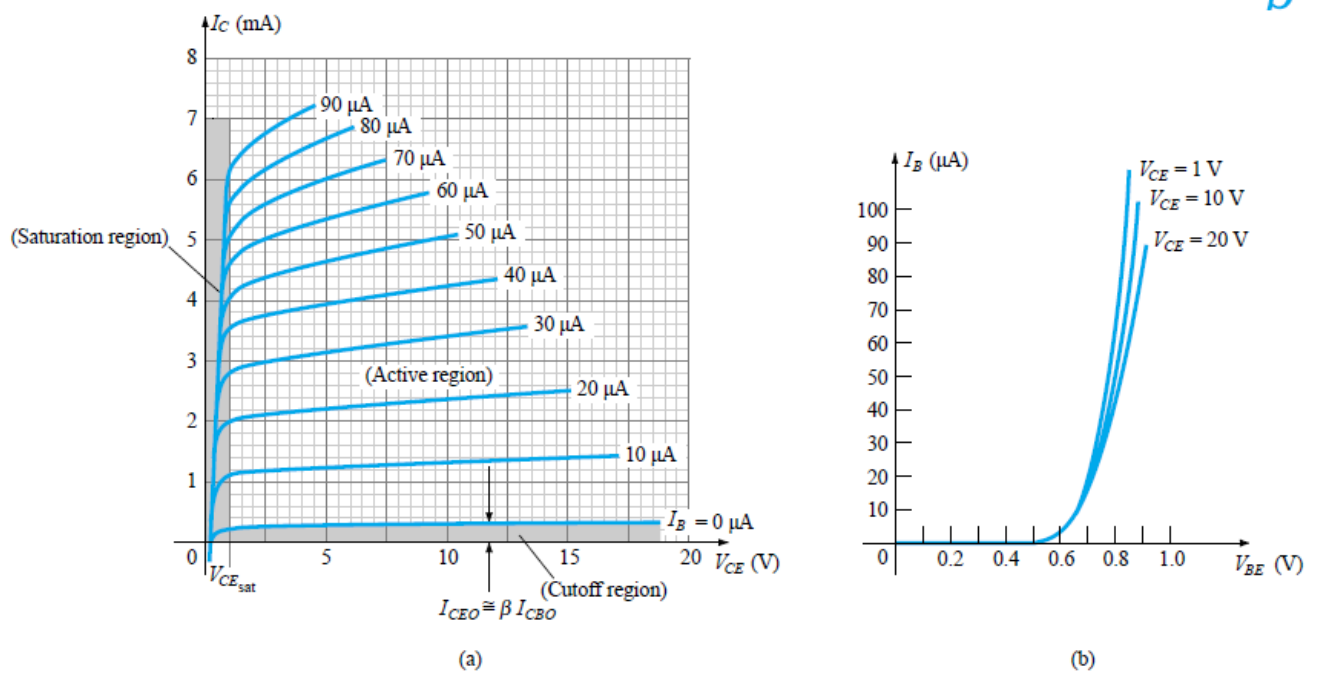
 $\beta$ 

Figure 3.8 Output or collector characteristics for a common-base transistor amplifier.

Q2.

- (a) Using the characteristics of Fig. 3.14, determine  $I_C$  at  $I_B = 30 \mu\text{A}$  and  $V_{CE} = 10 \text{ V}$ .
- (b) Using the characteristics of Fig. 3.14, determine  $I_C$  at  $V_{BE} = 0.7 \text{ V}$  and  $V_{CE} = 15 \text{ V}$ .



**Figure 3.14** Characteristics of a silicon transistor in the common-emitter configuration: (a) collector characteristics; (b) base characteristics.

Q3.

- (a) Using the characteristics of Fig. 3.8, determine the resulting collector current if  $I_E = 4.5 \text{ mA}$  and  $V_{CB} = 4 \text{ V}$ .
- (b) Repeat part (a) for  $I_E = 4.5 \text{ mA}$  and  $V_{CB} = 16 \text{ V}$ .
- (c) How have the changes in  $V_{CB}$  affected the resulting level of  $I_C$ ?
- (d) On an approximate basis, how are  $I_E$  and  $I_C$  related based on the results above?

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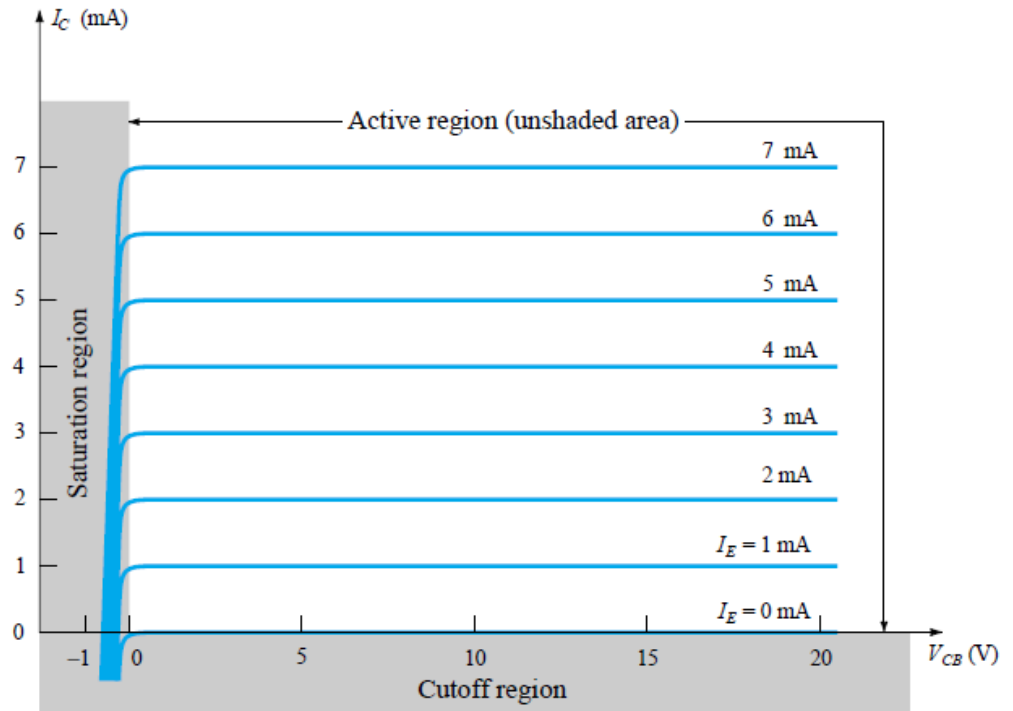


Figure 3.8 Output or collector characteristics for a common-base transistor amplifier.

Q4.

- (a) Using the characteristics of Figs. 3.7 and 3.8, determine  $I_C$  if  $V_{CB} = 10\text{ V}$  and  $V_{BE} = 800\text{ mV}$ .
- (b) Determine  $V_{BE}$  if  $I_C = 5\text{ mA}$  and  $V_{CB} = 10\text{ V}$ .

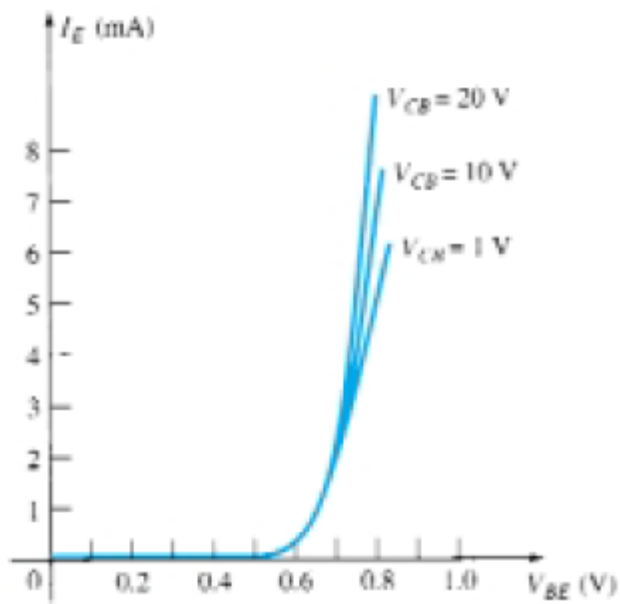


Figure 3.7 Input or driving point characteristics for a common-base silicon transistor amplifier.

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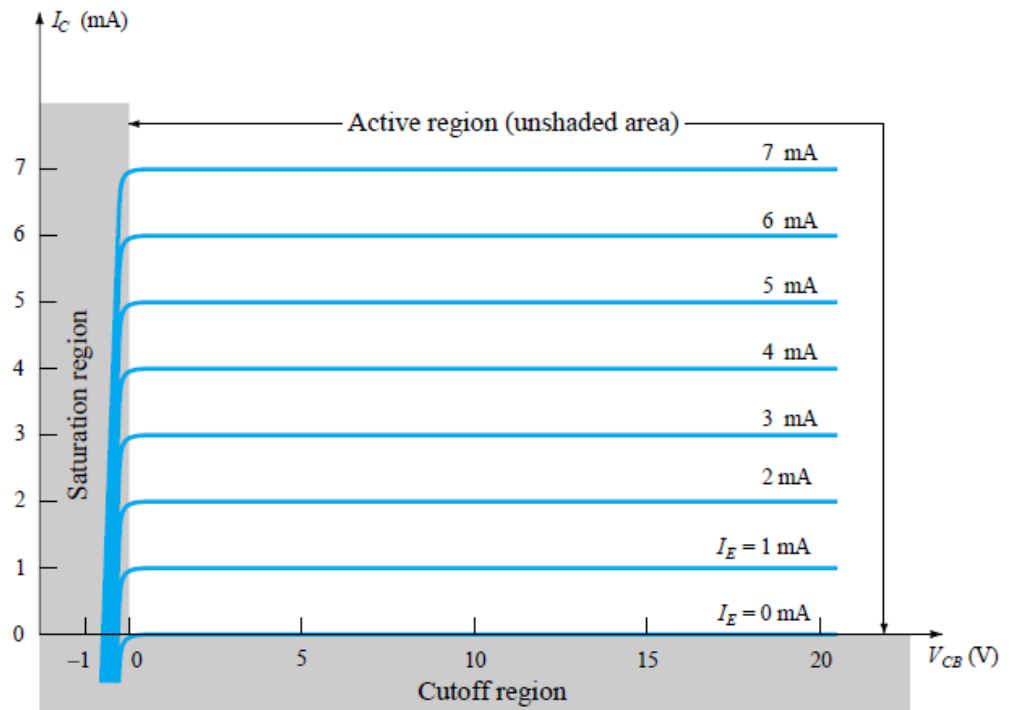


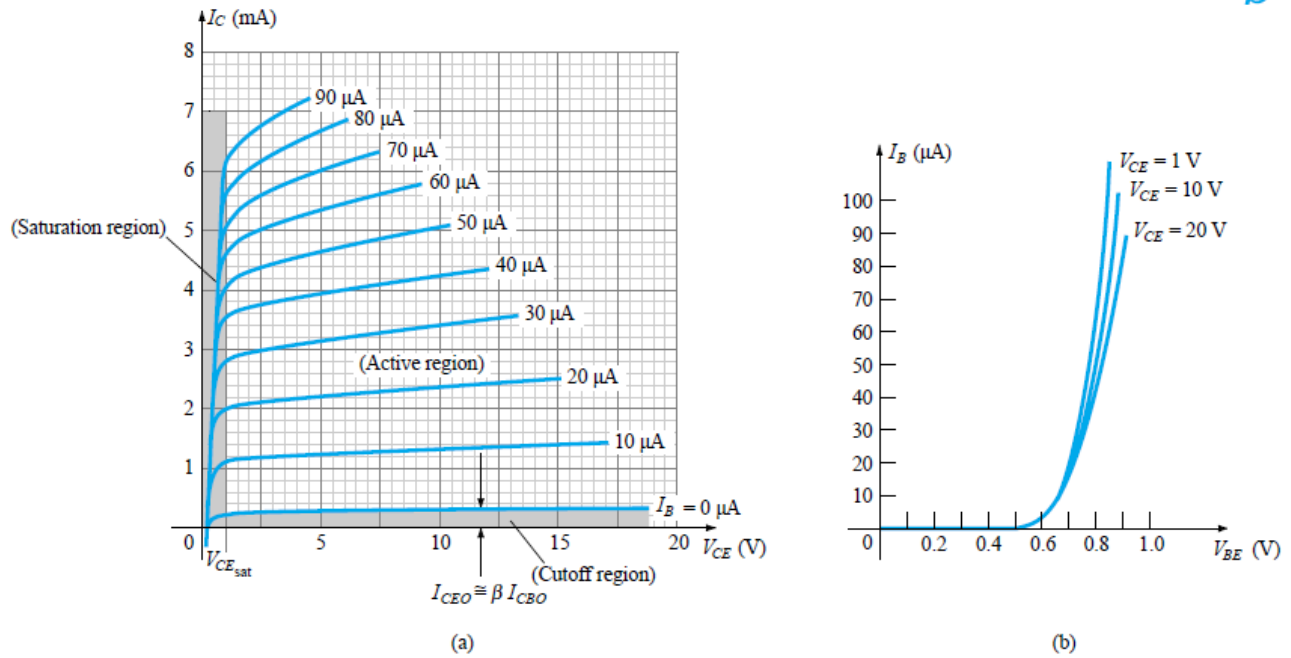
Figure 3.8 Output or collector characteristics for a common-base transistor amplifier.

Q5.

Using the characteristics of Fig. 3.14:

- Find the value of  $I_C$  corresponding to  $V_{BE} = +750$  mV and  $V_{CE} = +5$  V.
- Find the value of  $V_{CE}$  and  $V_{BE}$  corresponding to  $I_C = 3$  mA and  $I_B = 30$   $\mu$ A.

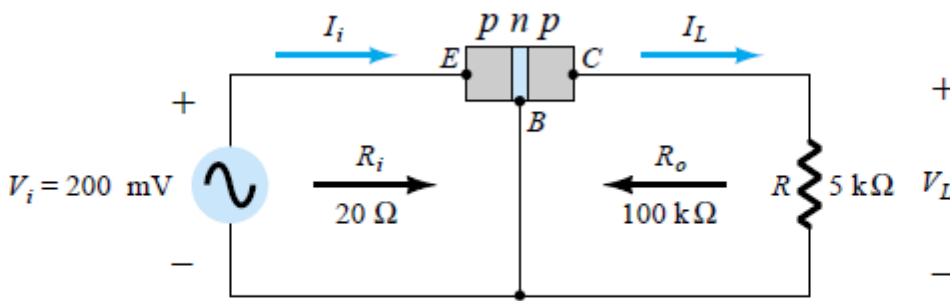
*B*



**Figure 3.14** Characteristics of a silicon transistor in the common-emitter configuration: (a) collector characteristics; (b) base characteristics.

Q6.

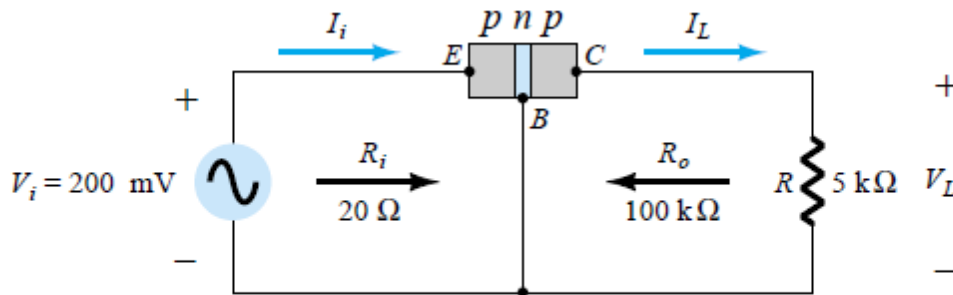
Calculate the voltage gain ( $A_v = V_L/V_i$ ) for the network of Fig. 3.12 if  $V_i = 500$  mV and  $R = 1$  k $\Omega$ . (The other circuit values remain the same.)



**Figure 3.12** Basic voltage amplification action of the common-base configuration.

Q7.

Calculate the voltage gain ( $A_v = V_L/V_i$ ) for the network of Fig. 3.12 if the source has an internal resistance of  $100\ \Omega$  in series with  $V_i$ .

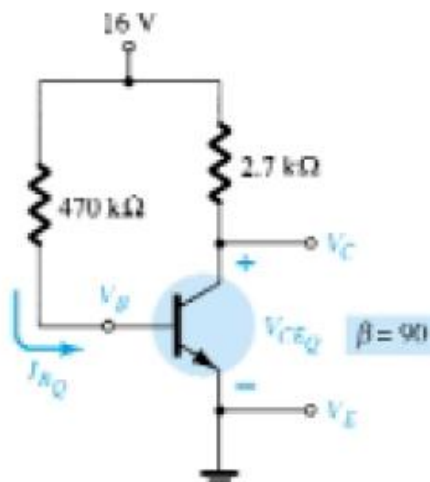


**Figure 3.12** Basic voltage amplification action of the common-base configuration.

Q8.

For the fixed-bias configuration of Fig. 4.73, determine:

- $I_{BQ}$
- $I_{CQ}$
- $V_{CEQ}$
- $V_C$
- $V_B$
- $V_E$



**Figure 4.73**  
47 51 52 53

Q9.

Given the information appearing in Fig. 4.74, determine:

- (a)  $I_C$ .
- (b)  $R_C$ .
- (c)  $R_B$ .
- (d)  $V_{CE}$ .

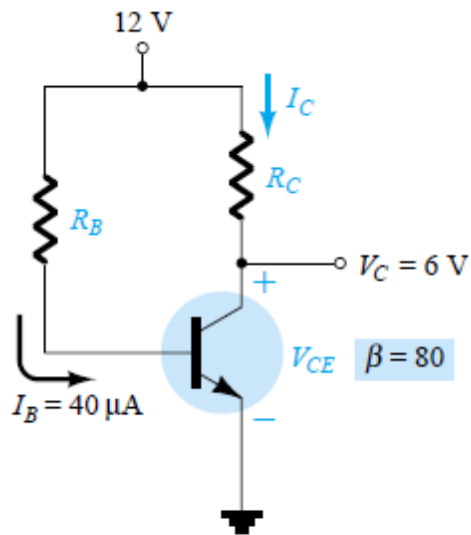


Figure 4.74 Problem 2

Q10.

Given the information appearing in Fig. 4.75, determine:

- (a)  $I_C$ .
- (b)  $V_{CC}$ .
- (c)  $\beta$ .
- (d)  $R_B$ .

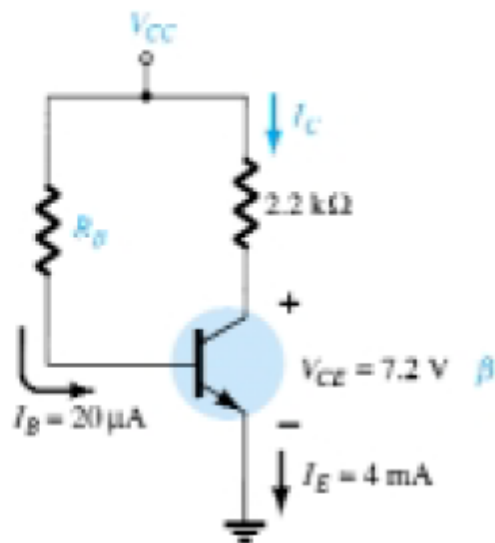


Figure 4.75 Problem 3

